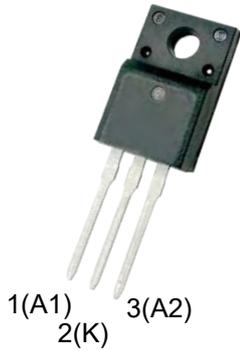
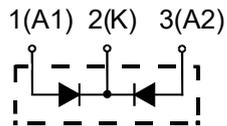


# HUR2020CTA1

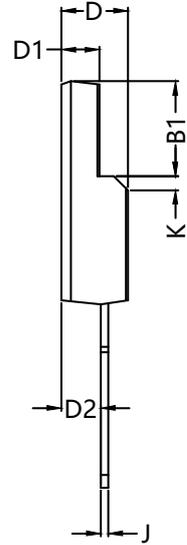
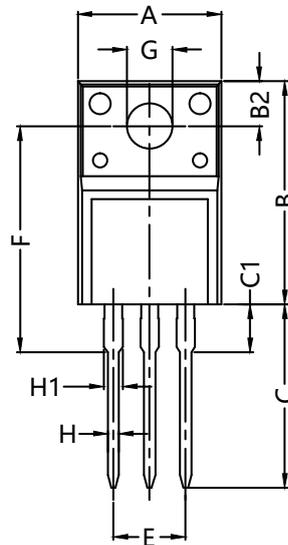
Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



Dimensions TO-220F



A1 = Anode 1  
A2 = Anode 2  
K = Cathode



|             | V <sub>RSM</sub><br>V | V <sub>RRM</sub><br>V |
|-------------|-----------------------|-----------------------|
| HUR2020CTA1 | 220                   | 200                   |

## ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter                            | Test Conditions                          | Values      | Unit |
|---------------------|--------------------------------------|--|-------------|------|
| V <sub>R</sub>      | Maximum D.C. Reverse Voltage         |  | 200         | V    |
| V <sub>RRM</sub>    | Maximum Repetitive Reverse Voltage   |  | 200         | V    |
| I <sub>F(AV)</sub>  | Average Forward Current              | T <sub>C</sub> =110°C, Per Diode         | 10          | A    |
|                     |                                      | T <sub>C</sub> =110°C, Per Package       | 20          | A    |
| I <sub>F(RMS)</sub> | RMS Forward Current                  | T <sub>C</sub> =110°C, Per Diode         | 14          | A    |
| I <sub>FSM</sub>    | Non-Repetitive Surge Forward Current | T <sub>J</sub> =45°C, t=10ms, 50Hz, Sine | 150         | A    |
| P <sub>D</sub>      | Power Dissipation                    |  | 80          | W    |
| T <sub>J</sub>      | Junction Temperature                 |  | -40 to +150 | °C   |
| T <sub>STG</sub>    | Storage Temperature Range            |  | -40 to +150 | °C   |
| R <sub>θJC</sub>    | Thermal Resistance                   | Junction-to-Case                         | 2.23        | °C/W |
| V <sub>ISO</sub>    | 1min / 1 sec                         | Terminal-to-Case                         | 2000/2500   | VAC  |
| Weight              |                                      |  | 2           | g    |



# HUR2020CTA1

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

| Symbol    | Parameter                     | Test Conditions   | Min. | Typ. | Max. | Unit          |
|-----------|-------------------------------|---|------|------|------|---------------|
| $I_{RM}$  | Reverse Leakage Current       | $V_R=200\text{V}$   | --   | --   | 10   | $\mu\text{A}$ |
|           |                               | $V_R=200\text{V}, T_J=125^\circ\text{C}$                          | --   | --   | 10   | $\text{mA}$   |
| $V_F$     | Forward Voltage               | $I_F=10\text{A}$  | --   | 0.90 | 1.10 | $\text{V}$    |
|           |                               | $I_F=10\text{A}, T_J=125^\circ\text{C}$                           | --   | --   | 0.95 | $\text{V}$    |
| $t_{rr}$  | Reverse Recovery Time         | $I_F=1\text{A}, V_R=30\text{V}, di_F/dt=-200\text{A}/\mu\text{s}$ | --   | 27   | 35   | $\text{ns}$   |
| $t_{rr}$  | Reverse Recovery Time         | $V_R=100\text{V}, I_F=10\text{A}$                                 | --   | 40   | 50   | $\text{ns}$   |
| $I_{RRM}$ | Max. Reverse Recovery Current | $di_F/dt=-200\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$          | --   | 2.1  | --   | $\text{A}$    |
| $t_{rr}$  | Reverse Recovery Time         | $V_R=100\text{V}, I_F=10\text{A} di_F/dt$                         | --   | 55   | 65   | $\text{ns}$   |
| $I_{RRM}$ | Max. Reverse Recovery Current | $dt=-200\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$              | --   | 5    | --   | $\text{A}$    |

### FEATURES

- \* International standard package **TO-220F**
- \* Planar passivated chips
- \* Very short recovery time
- \* Extremely low switching losses
- \* Low  $I_{RM}$ -values
- \* Soft recovery behaviour
- \* RoHS compliant
- \* This device may substitute for RF2001T2D series.

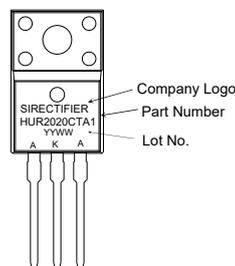
### APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Antisaturation diode
- \* Snubber diode
- \* Free wheeling diode in converters and motor control circuits
- \* Rectifiers in switch mode power supplies (SMPS)
- \* Inductive heating and melting
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses
- \* Operating at lower temperature or space saving by reduced cooling

### Marking



### Ordering Information

| Part Number | Package | Shipping     | Marking Code |
|-------------|---------|--------------|--------------|
| HUR2020CTA1 | TO-220F | 50pcs / Tube | HUR2020CTA1  |

**Sirectifier**<sup>®</sup>

# HUR2020CTA1

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

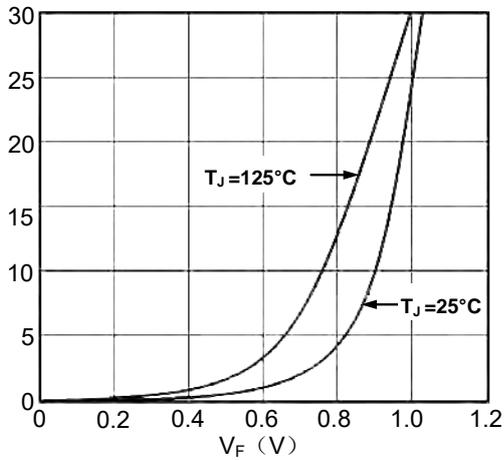


Fig1. Forward Voltage Drop vs Forward Current

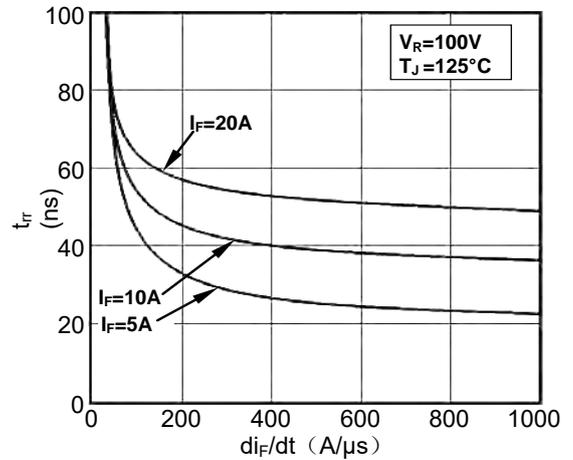


Fig2. Reverse Recovery Time vs  $di_F/dt$

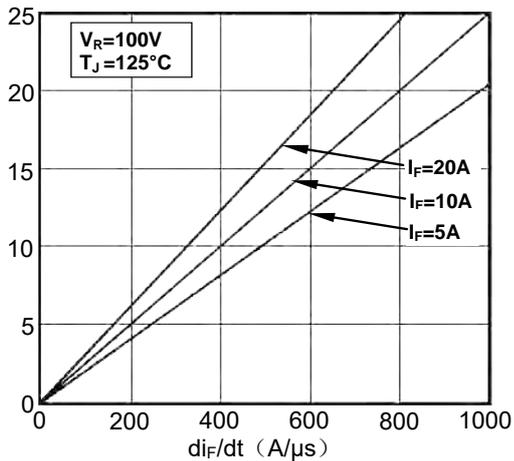


Fig3. Reverse Recovery Current vs  $di_F/dt$

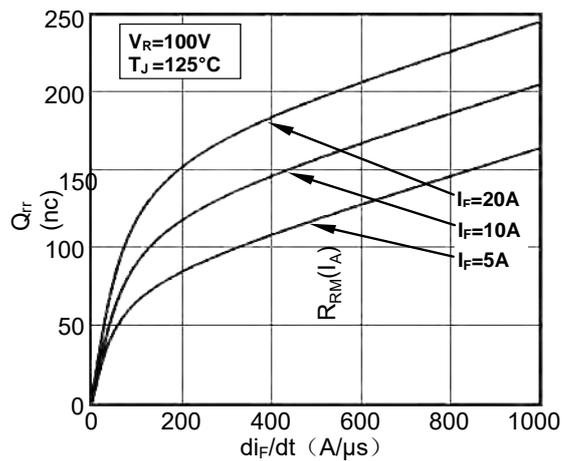


Fig4. Reverse Recovery Charge vs  $di_F/dt$

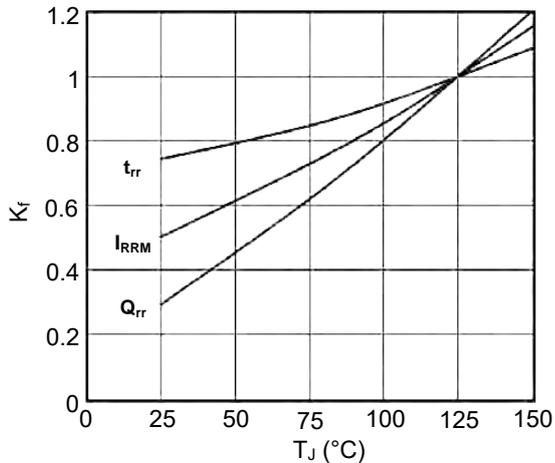


Fig5. Dynamic Parameters vs Junction Temperature

